



60V N-Channel Enhancement Mode MOSFET - ESD Protected

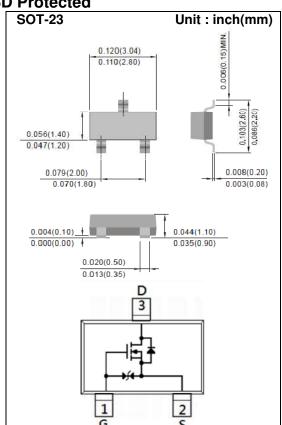
Voltage 60 V Current 300mA

Features

- $R_{DS(ON)}$, $V_{GS}@10V$, $I_{D}@500mA<3\Omega$
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_{D}@200mA<4\Omega$
- Advanced Trench Process Technology
- High Density Cell Design For Ultra Low On-Resistance
- Very Low Leakage Current In Off Condition
- Specially Designed for Battery Operated Systems, Solid-State Relays Drivers: Relay, Displays, Memories, etc
- ESD Protected 2KV HBM
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case: SOT-23 Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0003 ounces, 0.0084 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMET	SYMBOL	LIMIT	UNITS	
Drain-Source Voltage	V _{DS}	60	V	
Gate-Source Voltage	V _{GS}	<u>+</u> 20		
Continuous Drain Current (Note 4)	I _D	300	mA	
Pulsed Drain Current (Note 1)		I _{DM}		
Power Dissipation	T _A =25°C	Б	500	mW
	Derate above 25°C	P _D	4	mW/°C
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~150	۰C
Typical Thermal Resistance - Junction to Ambient (Note 3,4)		R _θ JA	250	°C/W





Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =10uA	60	-	-	_ v	
Gate Threshold Voltage	$V_{\text{GS(th)}}$	V _{DS} =V _{GS} , I _D =250uA	1	-	2.5 V		
Davis Os and Os Olate Davis		V _{GS} =10V,I _D =500mA	-	-	3	Ω	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =4.5V,I _D =200mA	-	-	4		
Zero Gate Voltage Drain Current	IDSS	V _{DS} =60V,V _{GS} =0V	-	-	1	uA	
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 10		
Forward Transconductance	G fs	V _{DS} =15V, I _D =250mA	100	-	ı	mS	
Dynamic (Note 5)							
Total Gate Charge	Q_g	V _{DS} =15V, I _D =250mA, V _{GS} =5V (Note 1,2)	-	0.8	i	nC	
Gate-Source Charge	Q_{gs}		-	0.35	-		
Gate-Drain Charge	Q_{gd}		-	0.2	ı		
Input Capacitance	Ciss)/ OF)/)/ O)/	-	35	ı	pF	
Output Capacitance	Coss	V _{DS} =25V, V _{GS} =0V, f=1MHZ	-	13	ı		
Reverse Transfer Capacitance	Crss		-	8	1		
Turn-On Delay Time	td _(on)		-	2.7	-	ns	
Turn-On Rise Time	tr	V_{DD} =30V, I_{D} =200mA, V_{GS} =10V, R_{G} =10Q (Note 1,2)	-	19	-		
Turn-Off Delay Time	td _(off)		-	15	ı		
Turn-Off Fall Time	tf	ng-1002 (***** *)=/	-	23	-		
Drain-Source Diode							
Maximum Continuous Drain-Source Diode Forward Current	ls		-	-	300	mA	
Diode Forward Voltage	V _{SD}	I _S =200mA, V _{GS} =0V	-	0.82	1.3	V	

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

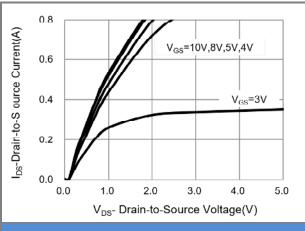


Fig.1 On-Region Characteristics

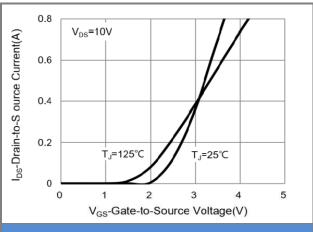


Fig.2 Transfer Characteristics

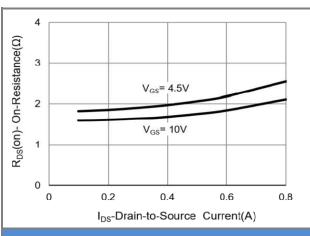


Fig.3 On-Resistance vs. Drain Current

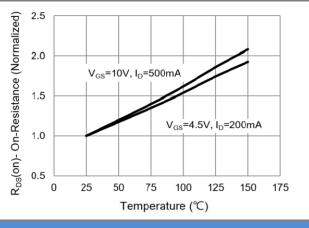
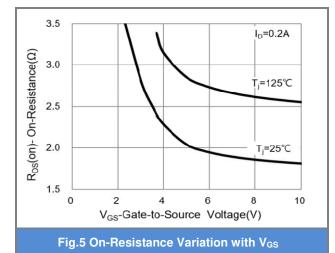
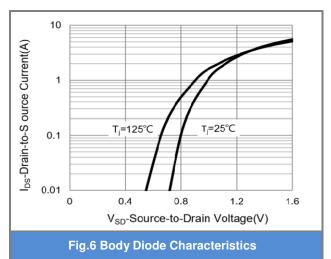


Fig.4 On-Resistance vs. Junction temperature









TYPICAL CHARACTERISTIC CURVES

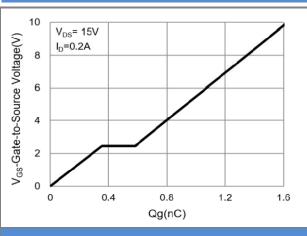


Fig.7 Gate-Charge Characteristics

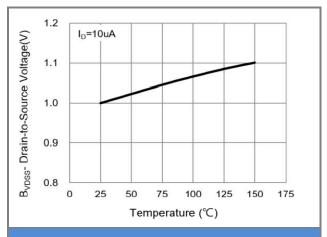


Fig.8 Breakdown Voltage Variation vs. Temperature

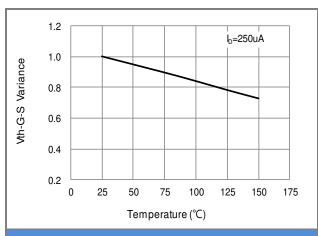


Fig.9 Threshold Voltage Variation with Temperature

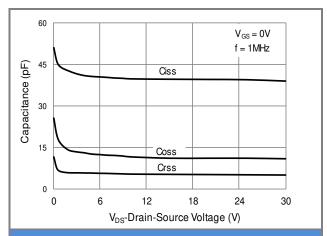


Fig.10 Capacitance vs. Drain-Source Voltage

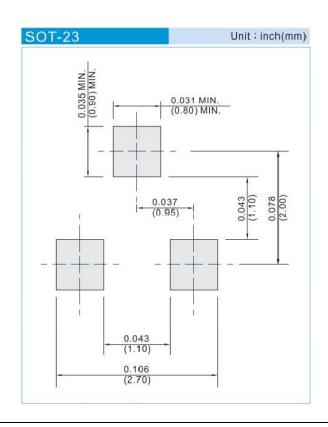




Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
2N7002K-AU_R1_000A2	SOT-23	3K pcs / 7" reel	K72	Halogen free

Mounting Pad Layout







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